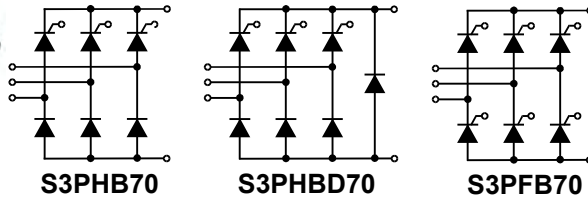
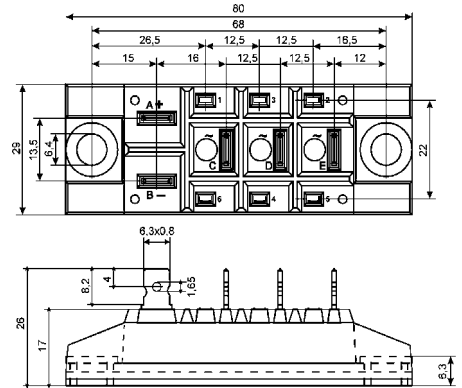


S3PHB70, S3PHBD70, S3PFB70

Three Phase Half Controlled Bridge Modules/Full Controlled Bridge



Dimensions in mm (1mm=0.0394")



Type	V_{RSM} V	V_{RRM} V
S3PHB70G08B	900	800
S3PHB70G12B	1300	1200
S3PHB70G14B	1500	1400
S3PHB70G16B	1700	1600

Symbol	Test Conditions	Maximum Ratings	Unit
I_{dAV} I_{dAVM} I_{FRMS}, I_{TRMS}	$T_c=85^\circ\text{C}$, module module per leg	70 70 36	A
I_{FSM}, I_{TSM}	$T_{VJ}=45^\circ\text{C}$ $V_R=0$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	550 600	A
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	500 550	
I^2t	$T_{VJ}=45^\circ\text{C}$ $V_R=0$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	1520 1520	A^2s
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	1250 1250	
$(di/dt)_{cr}$	$T_{VJ}=125^\circ\text{C}$ $f=50\text{Hz}$, $t_p=200\mu\text{s}$ $V_D=2/3V_{DRM}$ $I_G=0.3\text{A}$ $di_G/dt=0.3\text{A}/\mu\text{s}$	repetitive, $I_T=50\text{A}$ 500	A/ μs
	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise)	$V_{DR}=2/3V_{DRM}$ 1000	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$ $t_p=30\mu\text{s}$ $t_p=500\mu\text{s}$ $t_p=10\text{ms}$	10 5 1	W
T_{VJ} T_{VJM} T_{stg}		-40...+125 125 -40...+125	$^\circ\text{C}$
V_{ISOL}	50/60Hz, RMS $I_{ISOL}\leq 1\text{mA}$ $t=1\text{min}$ $t=1\text{s}$	2500 3000	V~
M_d	Mounting torque (M5) (10-32 UNF)	$5 \pm 15\%$ $44 \pm 15\%$	Nm/lb.in.
Weight	typical	95	g



S3PHB70, S3PHBD70, S3PFB70

Three Phase Half Controlled Bridge Modules/Full Controlled Bridge

Symbol	Test Conditions	Characteristic Values	Unit
$I_{D,IR}$	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
$V_{TA\#VFA}$	$I_{TM}, I_{FM}=70A; T_{VJ}=25^{\circ}C$ for every chip	1.64	V
V_{TO}	For power-loss calculations only	0.85	V
r_T		11	$m\Omega$
V_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
V_{GD}	$T_{VJ}=T_{VJM};$ $V_D=2/3V_{DRM}$	0.2	V
I_{GD}		5	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=20A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=15V/\mu s; V_D=2/3V_{DRM}$	250	μs
I_{RM}		45	A
R_{thJC}	per thyristor/diode; DC current per module	0.9 0.15	K/W
R_{thJK}	per thyristor/diode; DC current per module	1.1 0.157	K/W
d_s	Creeping distance on surface	16.1	mm
d_A	Strike distance through air	7.5	mm
a	Maximum allowable acceleration	50	m/s^2

FEATURES

- * Low forward voltage drop
- * Package with copper base plate
- * Glass passivated chips
- * Isolation voltage 3000 V~
- * 1/4" fast-on power terminals
- * UL File NO.E310749
- * RoHS compliant

APPLICATIONS

- * Input rectifiers for PWM inverter
- * Supplies for DC power equipment
- * Field supply for DC motors
- * Battery DC power supplies

ADVANTAGES

- * Space and weight savings
- * Easy to mount with two screws
- * Improved temperature and power cycling capability
- * Small and light weight

